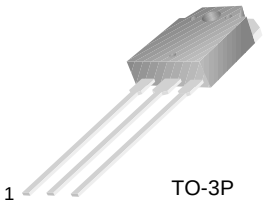
FAIRCHILD SEMICONDUCTOR™

TIP145/146/147

Monolithic Construction With Built In Base-Emitter Shunt Resistors

- High DC Current Gain : h_{FE} = 1000 @ V_{CE} = -4V, I_C = -5A (Min.)
- Industrial Use
- Complement to TIP140/141/142



TO-3P

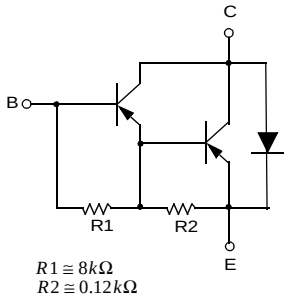
1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Darlington Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter		Value	Units
V_{CBO}	Collector-Base Voltage	: TIP145	- 60	V
		: TIP146	- 80	V
		: TIP147	- 100	V
V_{CEO}	Collector-Emitter Voltage	: TIP145	- 60	V
		: TIP146	- 80	V
		: TIP147	- 100	V
V_{EBO}	Emitter-Base Voltage		- 5	V
I_C	Collector Current (DC)		- 10	A
I_{CP}	Collector Current (Pulse)		- 15	A
I_B	Base Current (DC)		- 0.5	A
P_C	Collector Dissipation (T_C=25°C)		125	W
T_J	Junction Temperature		150	°C
T_{STG}	Storage Temperature		- 65 ~ 150	°C

Equivalent Circuit



$R1 \cong 8k\Omega$
$R2 \cong 0.12k\Omega$

Electrical Characteristics T_C=25°C **unless otherwise noted**

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V_{CEO}(sus)	Collector-Emitter Sustaining Voltage					
	: TIP145	I_C = - 30mA, I_B = 0	- 60			V
	: TIP146		- 80			V
	: TIP147		- 100			V
I_{CEO}	Collector Cut-off Curren					
	: TIP145	V_{CE} = - 30V, I_B = 0			- 2	mA
	: TIP146	V_{CE} = - 40V, I_B = 0			- 2	mA
	: TIP147	V_{CE} = - 50V, I_B = 0			- 2	mA
I_{CBO}	Collector Cut-off Current					
	: TIP145	V_{CB} = - 60V, I_E = 0			- 1	mA
	: TIP146	V_{CB} = - 80V, I_E = 0			- 1	mA
	: TIP147	V_{CB} = - 100V, I_E = 0			- 1	mA
I_{EBO}	Emitter Cut-off Current	V_{BE} = - 5V, I_C = 0			- 2	mA
h_{FE}	DC Current Gain	V_{CE} = - 4V,I_C = - 5A	1000			
		V_{CE} = - 4V, I_C = - 10A	500			
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = - 5A, I_B = - 10mA			- 2	V
		I_C = - 10A, I_B = - 40mA			- 3	V
V_{BE}(sat)	Base-Emitter Saturation Voltage	I_C = - 10A, I_B = - 40mA			- 3.5	V
V_{BE}(on)	Base-Emitter ON Voltage	V_{CE} = - 4V, I_C = - 10A			- 3	V
t_D	Delay Time	V_{CC} = - 30V, I_C = - 5A		0.15		µs
t_R	Rise Time	I_{B1}= -20mA, I_{B2} = 20mA		0.55		µs
t_{STG}	Storage Time	R_L = 6Ω		2.5		µs
t_F	Fall Time			2.5		µs

Typical Characteristics

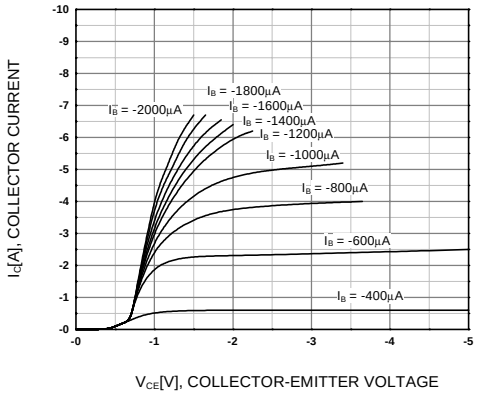


Figure 1. Static Characteristic

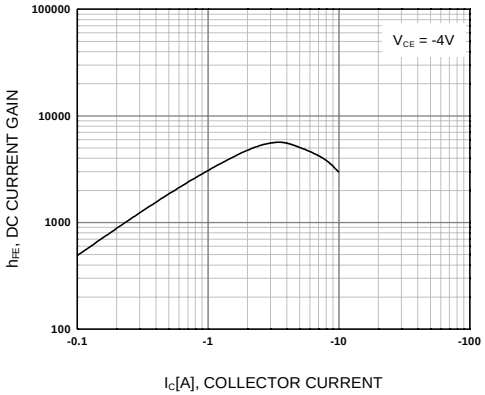


Figure 2. DC current Gain

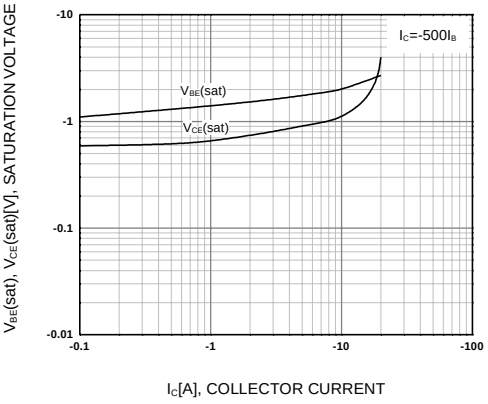


Figure 3. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

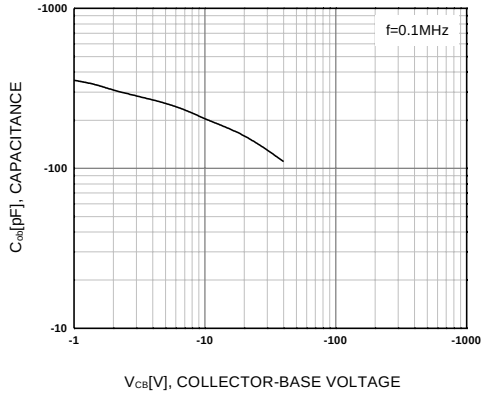


Figure 4. Collector Output Capacitance

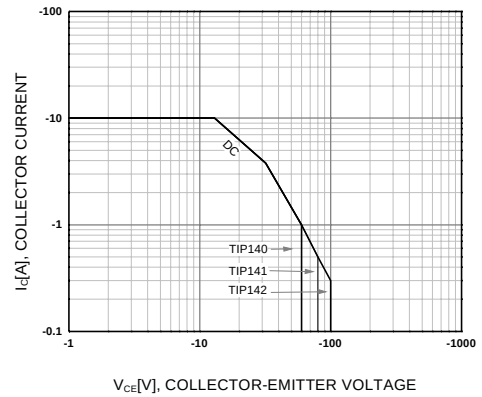


Figure 5. Safe Operating Area

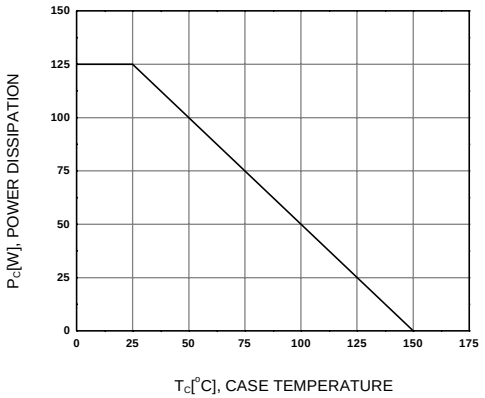
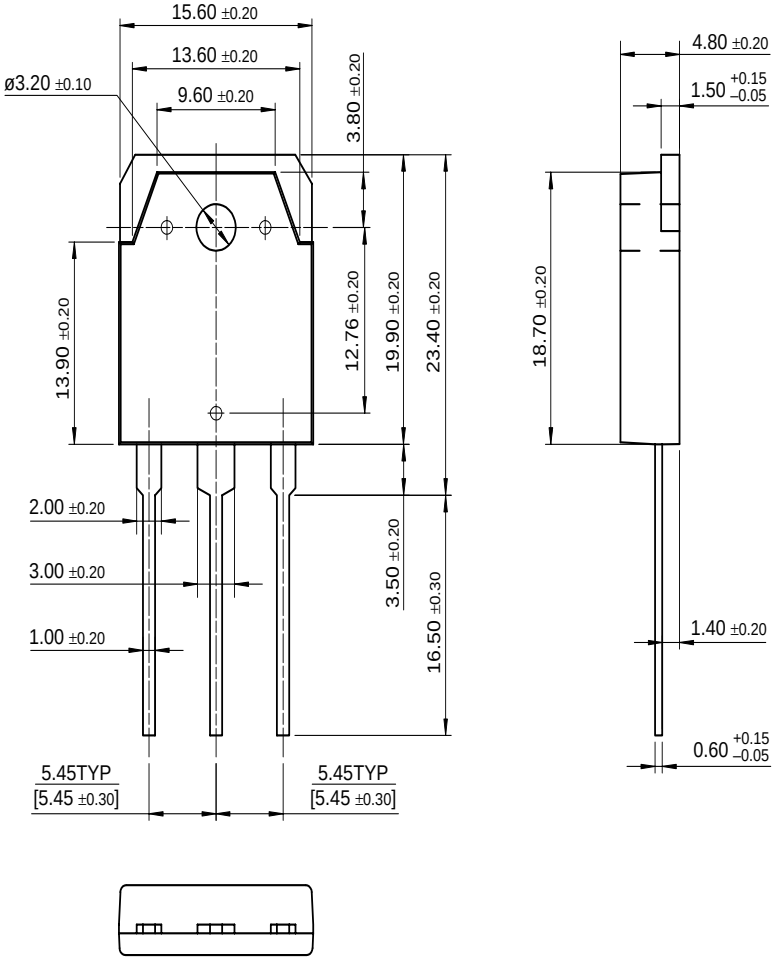


Figure 6. Power Derating

Package Demensions

TO-3P



Dimensions in Millimeters

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